

Notice of References Cited	Application/Control No. 10/762,181	Applicant(s)/Patent Under Reexamination MOKHLESI ET AL.	
	Examiner Huan Hoang	Art Unit 2827	Page 1 of 1

U.S. PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
*	A	US-6,784,484	08-2004	Blomme et al.	257/321
*	B	US-6,790,782	09-2004	Yang et al.	438/706
	C	US-			
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	E	US-			
	F	US-			
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	H	US-			
	I	US-			
	J	US-			
	K	US-			
	L	US-			
	M	US-			

FOREIGN PATENT DOCUMENTS

*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Country	Name	Classification
	N					
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NON-PATENT DOCUMENTS

*		Include as applicable: Author, Title Date, Publisher, Edition or Volume, Pertinent Pages)
*	U	"An Empeirical Model for Charge Leakage Through Oxide-Nitride-Oxide Interpoly Dielectric In Stacked-Gate Flash Memory Devices", Jang Han Kim, Jung Bum Choi, Bong Jo Shin and Kuen Hyung Park, Semiconductor Science and Technology 18 (2003) pp. 258-162.
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*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.